HFA3134, HFA3135



Data Sheet

August 12, 2005

Ultra High Frequency Matched Pair Transistors

The HFA3134 and HFA3135 are Ultra High Frequency Transistor pairs that are fabricated with Intersil Corporation's complementary bipolar UHF-1X process. The NPN transistors exhibit an f_T of 8.5GHz, while the PNP transistors have an f_T of 7GHz. Both types exhibit low noise, making them ideal for high frequency amplifier and mixer applications.

Both arrays are matched high frequency transistor pairs. The matching simplifies DC bias problems and it minimizes imbalances in differential amplifier configurations. Their high f_T enables the design of UHF amplifiers which exhibit exceptional stability.

Ordering Information

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
HFA3134IH96 (04/†0)	-40 to 85	6 Ld SOT23 Tape and Reel	P6.064
HFA3134IHZ96 (4Z/Z⊅) (Note)	-40 to 85	6 Ld SOT23 Tape and Reel (Pb-free)	P6.064
HFA3135IH96 (05/90)	-40 to 85	6 Ld SOT23 Tape and Reel	P6.064
HFA3135IHZ96 (5Z/9Z) (Note)	-40 to 85	6 Ld SOT23 Tape and Reel (Pb-free)	P6.064

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

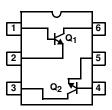
•	NPN Transistor (f _T)8.50	GHz
•	NPN Current Gain (h _{FE})	100
•	NPN Noise Figure (50 Ω) at 1.0GHz2.	6dB
•	PNP Transistor (f _T)	GHz
•	PNP Current Gain (h _{FE})	. 57
•	PNP Noise Figure (50 Ω) at 900MHz 4.	6dB
•	Small Package (EIAJ-SC74 Compliant)SOT2	23-6
•	Pb-Free Plus Anneal Available (RoHS Compliant)	

Applications

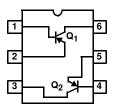
- VHF/UHF Amplifiers
- VHF/UHF Mixers
- IF Converters
- · Synchronous Detectors

Pinouts





HFA3135 (SOT23) TOP VIEW



Absolute Maximum Ratings

$ \begin{array}{llllllllllllllllllllllllllllllllllll$
26mA at T _J =125°C
Base Current (Note 2)1.7mA
ESD Rating
Human Body Model400V (Per MIL-STD-883 Method 3015.7)

Operating Conditions

Temperature Range-40°C to 85°C

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
SOT23-6 Package	. 350
Maximum Junction Temperature (Die)	
Maximum Junction Temperature (Plastic Package) .	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature	
(Soldering 10s, Lead Tips Only)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- 1. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.
- 2. If a transistor is used in a diode configuration, the collector must be connected to the base to avoid exceeding the maximum base current specification.

Electrical Specifications T_A = 25°C

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	ТҮР	MAX	UNITS
DC CHARACTERISTICS FOR HFA3134 (NPN)		1			1	1	1
Collector to Base Breakdown Voltage	V _{(BR)CBO}	$I_{C} = 10 \mu A, I_{E} = 0$	А	12	21	-	V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 100μA, I _B = 0	А	4	9	-	V
	V _{(BR)CER}	I_{C} = 100μA, R _B = 10kΩ	А	11	17	-	V
Emitter to Base Breakdown Voltage (Note 4)	V _{(BR)EBO}	$I_{E} = 10 \mu A, I_{C} = 0$	В	-	6	-	V
Collector-Cutoff-Current	I _{CEO}	V _{CE} = 6V, I _B = 0	А	-5	-	5	nA
Collector-Cutoff-Current	I _{CBO}	V _{CB} = 8V, I _E = 0	А	-5	-	5	nA
Emitter-Cutoff-Current (Note 5)	I _{EBO}	V _{EB} = 1V, I _C = 0	В	-	1	-	pА
Collector to Collector Leakage			С	-	1	-	nA
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C = 10mA, I _B = 1mA	А	-	95	250	mV
Base to Emitter Voltage (Note 5)	V _{BE}	I _C = 10mA, V _{CE} = 2V	А	-	780	1000	mV
Q_1 to Q_2 Base to Emitter Voltage Match	ΔV_{BE}	I _C = 10mA, V _{CE} = 2V	А	-	1.2	6	mV
(Note 5)		I _C = 1mA, V _{CE} = 2V	А	-	1.0	6	mV
		I _C = 0.1mA, V _{CE} = 2V	А	-	0.7	6	mV
Base to Emitter Voltage Drift		I _C = 10mA	С	-	-1.5	-	mV/°C
DC Forward-Current Transfer Ratio	h _{FE}	I _C = 10mA, V _{CE} = 2V	А	48	80	200	
(Note 5)		I _C = 1mA, V _{CE} = 2V	А	48	87	200	
		I _C = 0.1mA, V _{CE} = 2V	А	48	90	200	
		I _C = 10mA, V _{CE} = 5V	А	48	96	200	
		I _C = 1mA, V _{CE} = 5V	А	48	96	200	
		I _C = 0.1mA, V _{CE} = 5V	А	48	100	200	
Q_1 to Q_2 Current Transfer Ratio Match	Δh_{FE}	$\begin{array}{l} 1mA \leq I_C \leq 10mA, \\ 1V \leq V_{CE} \leq 5V \end{array}$	A	-	2	8	%
Early Voltage	V _A	I _C = 1mA, ΔV _{CE} = 3V	А	20	30	-	V

Electrical Specifications $T_A = 25^{\circ}C$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	ТҮР	МАХ	UNITS
DYNAMIC CHARACTERISTICS FOR HFA				iiiiii			UNITO
Noise Figure	NF	$\label{eq:constraint} \begin{array}{l} f = 1.0GHz, \ I_C = 10mA, \\ 1V \leq V_{CE} \leq 5V, \ Z_S = 50\Omega \end{array}$	В	-	2.4	-	dB
		$\label{eq:f} \begin{array}{l} f = 1.0GHz, \ I_C = 1mA, \\ 1V \leq V_{CE} \leq 5V, \ Z_S = 50\Omega \end{array}$	В	-	2.6	-	dB
Current Gain-Bandwidth Product	f _T	I _C = 10mA, V _{CE} = 5V	В	-	8.5	-	GHz
(Note 5)		I _C = 1mA, V _{CE} = 5V	В	-	3	-	GHz
Power Gain-Bandwidth Product	f _{MAX}	I _C = 10mA, V _{CE} = 5V	В	-	7.5	-	GHz
Base to Emitter Capacitance		V _{BE} = -0.5V	В	-	600	-	fF
Collector to Base Capacitance		V _{CB} = 3V	В	-	500	-	fF

Electrical Specifications T_A = 25°C

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	ТҮР	MAX	UNITS
DC CHARACTERISTICS FOR HFA3135 (PNP))						
Collector to Base Breakdown Voltage	V _{(BR)CBO}	I _C = -10μΑ, I _E = 0	A	12	21	-	V
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = -100μA, I _B = 0	А	4	14	-	V
	V _{(BR)CER}	I_{C} = -100μA, R _B = 10kΩ	А	11	23	-	V
Emitter to Base Breakdown Voltage (Note 4)	V _{(BR)EBO}	$I_{E} = -10 \mu A, I_{C} = 0$	В	-	5	-	V
Collector-Cutoff-Current	ICEO	$V_{CE} = -6V, I_B = 0$	А	-5	-	5	nA
Collector-Cutoff-Current	I _{CBO}	$V_{CB} = -8V, I_E = 0$	А	-5	-	5	nA
Emitter-Cutoff-Current	I _{EBO}	V _{EB} = -1V, I _C = 0	В	-	TBD	-	pА
Collector to Collector Leakage			В	-	1	-	nA
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C = -10mA, I _B = -1mA	А	-	150	250	mV
Base to Emitter Voltage	V _{BE}	I _C = -10mA, V _{CE} = -2V	А	-	850	1000	mV
Q_1 to Q_2 Base to Emitter Voltage Match	ΔV_{BE}	I _C = -10mA, V _{CE} = -2V	А	-	1	6	mV
		I _C = -1mA, V _{CE} = -2V	А	-	1	6	mV
		I _C = -0.1mA, V _{CE} = -2V	А	-	2	6	mV
DC Forward-Current Transfer Ratio	h _{FE}	I _C = -10mA, V _{CE} = -2V	А	15	40	125	
		I _C = -1mA, V _{CE} = -2V	А	15	47	125	
		I _C = -0.1mA, V _{CE} = -2V	А	15	52	125	
		I _C = -10mA, V _{CE} = -5V	А	15	47	125	
		I _C = -1mA, V _{CE} = -5V	А	15	53	125	
		I _C = -0.1mA, V _{CE} = -5V	A	15	57	125	
Q_1 to Q_2 Current Gain Match	Δh_{FE}	$\begin{array}{l} \text{-1mA} \leq I_C \leq \text{-10mA}, \\ \text{-1V} \leq V_{CE} \leq \text{-5V} \end{array}$	A	-	1	8	%
Early Voltage	VA	I_C = -1mA, ΔV_{CE} = -3V	А	15	24	-	V
Base to Emitter Voltage Drift		I _C = -10mA	С	-	-1.4	-	mV/°C

Electrical Specifications $T_A = 25^{\circ}C$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	(NOTE 3) TEST LEVEL	MIN	ТҮР	MAX	UNITS	
DYNAMIC CHARACTERISTICS FOR HFA3135 (PNP)								
Noise Figure	NF	$\label{eq:states} \begin{array}{l} f = 900MHz, \ I_C = -10mA, \\ -1V \leq V_{CE} \leq -5V, \ Z_S = 50\Omega \end{array}$	В	-	5.2	-	dB	
		$\label{eq:states} \begin{array}{l} f = 900MHz, \ I_C = -1mA, \\ -1V \leq V_{CE} \leq -5V, \ Z_S = 50\Omega \end{array}$	В	-	4.6	-	dB	
Current Gain-Bandwidth Product	f _T	I _C = -10mA, V _{CE} = -5V	В	-	7	-	GHz	
Power Gain-Bandwidth Product	f _{MAX}	I _C = -10mA, V _{CE} = -5V	В	-	TBD	-	GHz	
Base to Emitter Capacitance		V _{BE} = 0.5V	В	-	550	-	fF	
Collector to Base Capacitance		V _{CB} = -3V	В	-	400	-	fF	

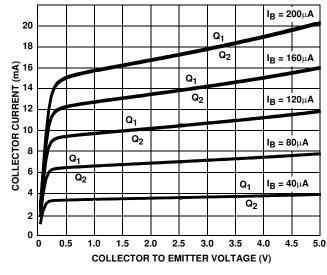
NOTES:

3. Test Level: A. Production Tested; B. Typical or Guaranteed Limit Based on Characterization; C. Design Typical for Information Only.

4. Measuring $V_{\mbox{EBO}}$ can degrade the transistor $h_{\mbox{FE}}$ and $h_{\mbox{FE}}$ match.

5. See Typical Performance Curves for more information.







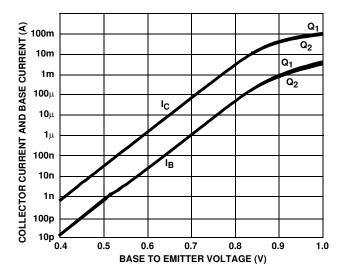


FIGURE 2. NPN COLLECTOR AND BASE CURRENTS vs BASE TO EMITTER VOLTAGE

Typical Performance Curves $T_A = 25^{\circ}C$, Unless Otherwise Specified (Continued)

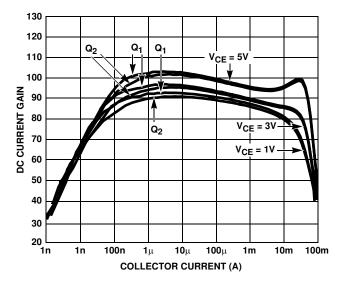


FIGURE 3. NPN DC CURRENT GAIN vs COLLECTOR CURRENT

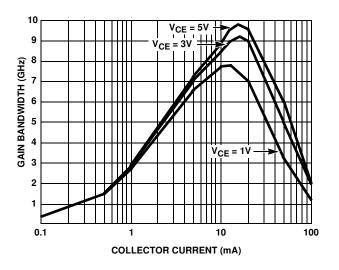


FIGURE 4. NPN GAIN BANDWIDTH PRODUCT vs COLLECTOR CURRENT

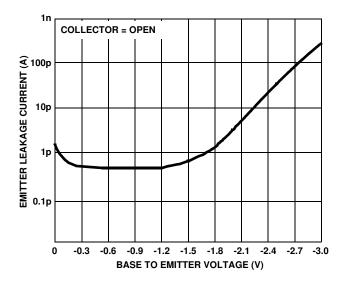


FIGURE 5. NPN EMITTER CUTOFF CURRENT vs BASE TO EMITTER VOLTAGE

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